

# N-Channel 200 V (D-S) 175 °C MOSFET

## PRODUCT SUMMARY

| $V_{DS}$ (V) | $R_{DS(on)}$ ( $\Omega$ ) | $I_D$ (A) |
|--------------|---------------------------|-----------|
| 200          | 0.090 at $V_{GS} = 10$ V  | 19        |
|              | 0.105 at $V_{GS} = 6$ V   | 17.5      |

## FEATURES

- TrenchFET® Power MOSFET
- 175 °C Junction Temperature
- PWM Optimized
- 100 %  $R_g$  Tested
- Compliant to RoHS Directive 2002/95/EC

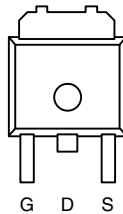


**RoHS**  
COMPLIANT

## APPLICATIONS

- Primary Side Switch

TO-252

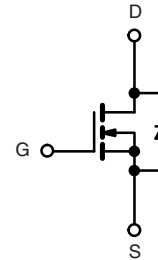


Top View

Drain Connected to Tab

### Ordering Information:

SUD19N20-90-E3 (Lead (Pb)-free)



N-Channel MOSFET

## ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)

| Parameter                                               | Symbol         | Limit            | Unit |
|---------------------------------------------------------|----------------|------------------|------|
| Drain-Source Voltage                                    | $V_{DS}$       | 200              | V    |
| Gate-Source Voltage                                     | $V_{GS}$       | $\pm 20$         |      |
| Continuous Drain Current ( $T_J = 175$ °C) <sup>b</sup> | $I_D$          | 19               | A    |
|                                                         |                | 11               |      |
| Pulsed Drain Current                                    | $I_{DM}$       | 40               |      |
| Continuous Source Current (Diode Conduction)            | $I_S$          | 19               |      |
| Avalanche Current                                       | $I_{AS}$       | 19               |      |
| Single Pulse Avalanche Energy                           | $E_{AS}$       | 18               | mJ   |
| Maximum Power Dissipation                               | $P_D$          | 136 <sup>b</sup> | W    |
|                                                         |                | 3 <sup>a</sup>   |      |
| Operating Junction and Storage Temperature Range        | $T_J, T_{stg}$ | - 55 to 175      | °C   |

## THERMAL RESISTANCE RATINGS

| Parameter                        | Symbol     | Typical | Maximum | Unit |
|----------------------------------|------------|---------|---------|------|
| Junction-to-Ambient <sup>a</sup> | $R_{thJA}$ | 15      | 18      | °C/W |
|                                  |            | 40      | 50      |      |
| Junction-to-Case (Drain)         | $R_{thJC}$ | 0.85    | 1.1     |      |

Notes:

a. Surface mounted on 1" x 1" FR4 board.

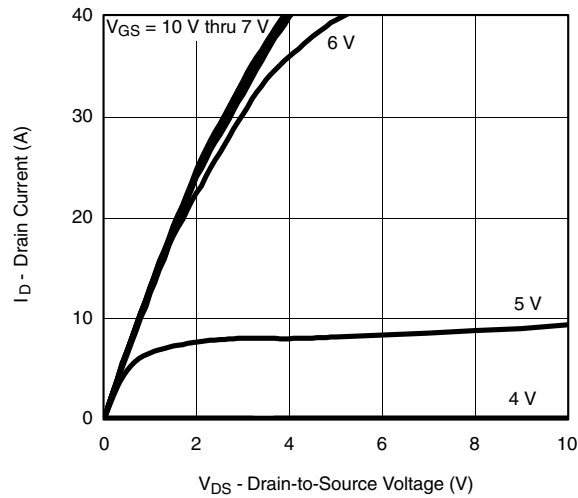
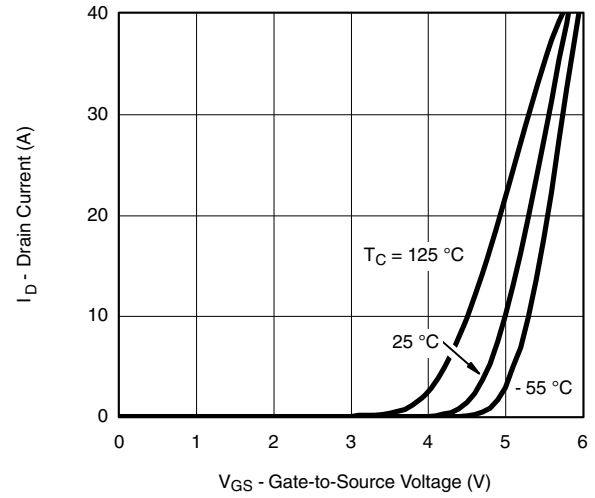
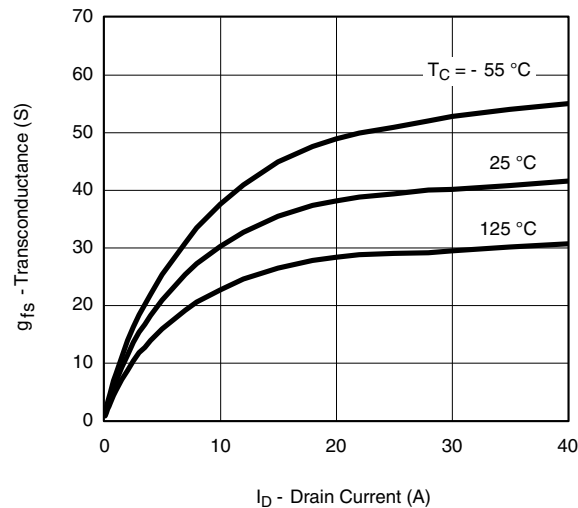
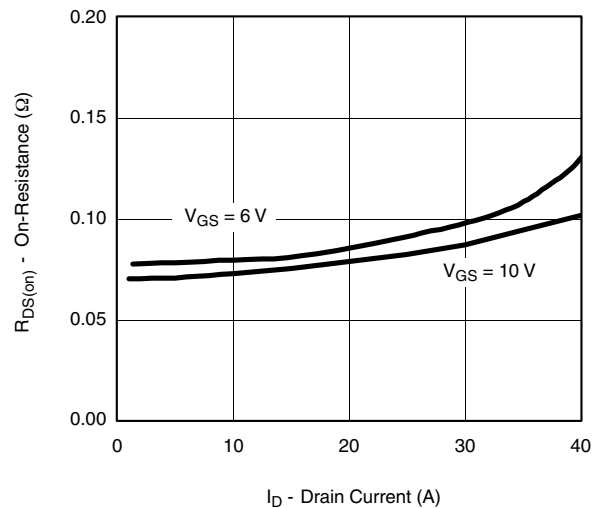
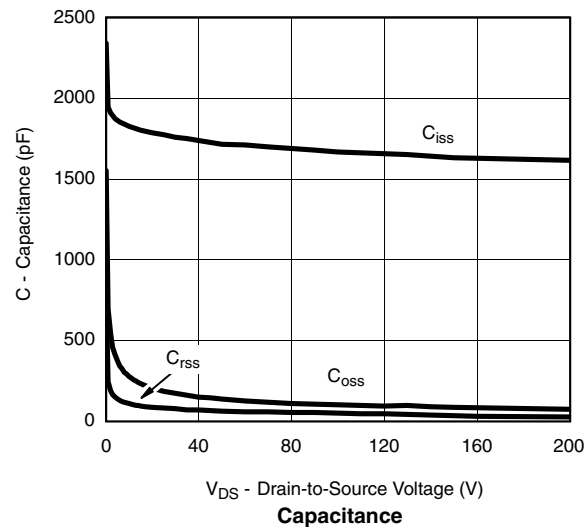
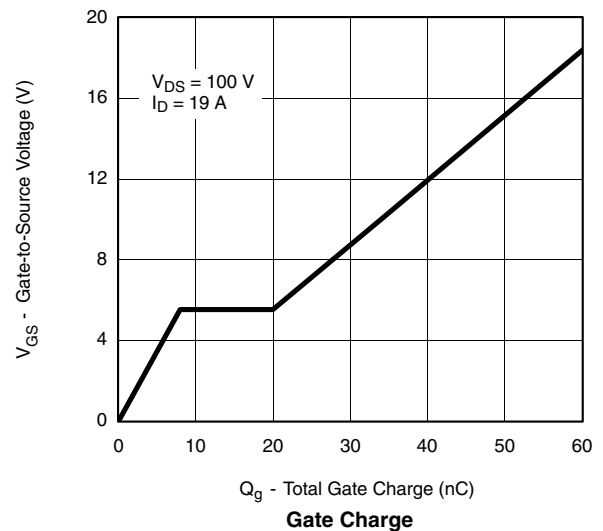
b. See SOA curve for voltage derating.

| SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)         |                     |                                                                                                                           |      |                   |       |      |
|-------------------------------------------------------------------------|---------------------|---------------------------------------------------------------------------------------------------------------------------|------|-------------------|-------|------|
| Parameter                                                               | Symbol              | Test Conditions                                                                                                           | Min. | Typ. <sup>a</sup> | Max.  | Unit |
| Static                                                                  |                     |                                                                                                                           |      |                   |       |      |
| Drain-Source Breakdown Voltage                                          | V <sub>DS</sub>     | V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA                                                                            | 200  |                   |       | V    |
| Gate Threshold Voltage                                                  | V <sub>GS(th)</sub> | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA                                                               | 2    |                   | 4     |      |
| Gate-Body Leakage                                                       | I <sub>GSS</sub>    | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V                                                                           |      |                   | ± 100 | nA   |
| Zero Gate Voltage Drain Current                                         | I <sub>DSS</sub>    | V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0 V                                                                            |      |                   | 1     | μA   |
|                                                                         |                     | V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C                                                   |      |                   | 50    |      |
|                                                                         |                     | V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C                                                   |      |                   | 250   |      |
| On-State Drain Current <sup>b</sup>                                     | I <sub>D(on)</sub>  | V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V                                                                             | 40   |                   |       | A    |
| Drain-Source On-State Resistance <sup>b</sup>                           | R <sub>DS(on)</sub> | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 5 A                                                                              |      | 0.075             | 0.090 | Ω    |
|                                                                         |                     | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 5 A, T <sub>J</sub> = 125 °C                                                     |      |                   | 0.190 |      |
|                                                                         |                     | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 5 A, T <sub>J</sub> = 175 °C                                                     |      |                   | 0.260 |      |
|                                                                         |                     | V <sub>GS</sub> = 6 V, I <sub>D</sub> = 5 A                                                                               |      | 0.082             | 0.105 |      |
| Forward Transconductance <sup>b</sup>                                   | g <sub>fs</sub>     | V <sub>DS</sub> = 15 V, I <sub>D</sub> = 19 A                                                                             |      | 35                |       | S    |
| Dynamic <sup>a</sup>                                                    |                     |                                                                                                                           |      |                   |       |      |
| Input Capacitance                                                       | C <sub>iss</sub>    | V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, F = 1 MHz                                                                  |      | 1800              |       | pF   |
| Output Capacitance                                                      | C <sub>oss</sub>    |                                                                                                                           |      | 180               |       |      |
| Reverse Transfer Capacitance                                            | C <sub>rss</sub>    |                                                                                                                           |      | 80                |       |      |
| Total Gate Charge <sup>c</sup>                                          | Q <sub>g</sub>      | V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 19 A                                                    |      | 34                | 51    | nC   |
| Gate-Source Charge <sup>c</sup>                                         | Q <sub>gs</sub>     |                                                                                                                           |      | 8                 |       |      |
| Gate-Drain Charge <sup>c</sup>                                          | Q <sub>gd</sub>     |                                                                                                                           |      | 12                |       |      |
| Gate Resistance                                                         | R <sub>g</sub>      |                                                                                                                           | 0.5  |                   | 2.9   | Ω    |
| Turn-On Delay Time <sup>c</sup>                                         | t <sub>d(on)</sub>  | V <sub>DD</sub> = 100 V, R <sub>L</sub> = 5.2 Ω<br>I <sub>D</sub> ≅ 19 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 2.5 Ω |      | 15                | 25    | ns   |
| Rise Time <sup>c</sup>                                                  | t <sub>r</sub>      |                                                                                                                           |      | 50                | 75    |      |
| Turn-Off Delay Time <sup>c</sup>                                        | t <sub>d(off)</sub> |                                                                                                                           |      | 30                | 45    |      |
| Fall Time <sup>c</sup>                                                  | t <sub>f</sub>      |                                                                                                                           |      | 60                | 90    |      |
| Source-Drain Diode Ratings and Characteristics (T <sub>C</sub> = 25 °C) |                     |                                                                                                                           |      |                   |       |      |
| Pulsed Current                                                          | I <sub>SM</sub>     |                                                                                                                           |      |                   | 50    | A    |
| Diode Forward Voltage <sup>b</sup>                                      | V <sub>SD</sub>     | I <sub>F</sub> = 19 A, V <sub>GS</sub> = 0 V                                                                              |      | 0.9               | 1.5   | V    |
| Source-Drain Reverse Recovery Time                                      | t <sub>rr</sub>     | I <sub>F</sub> = 19 A, dI/dt = 100 A/μs                                                                                   |      | 180               | 250   | ns   |

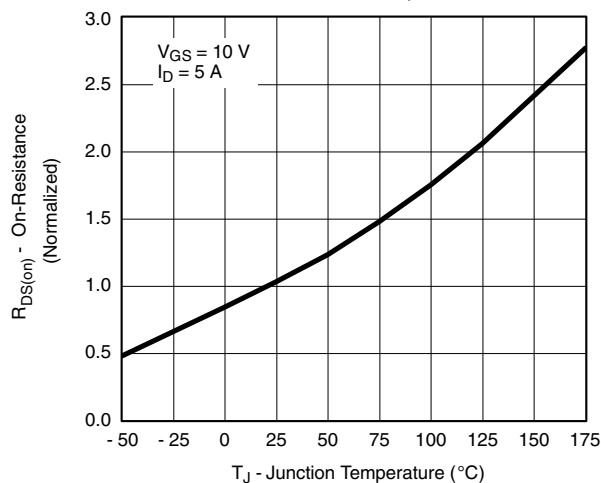
## Notes:

- a. Guaranteed by design, not subject to production testing.  
b. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
c. Independent of operating temperature.

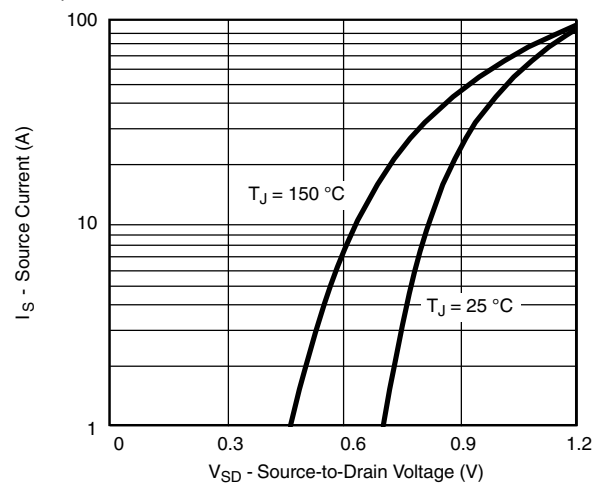
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Output Characteristics**

**Transfer Characteristics**

**Transconductance**

**On-Resistance vs. Drain Current**

**Capacitance**

**Gate Charge**

## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

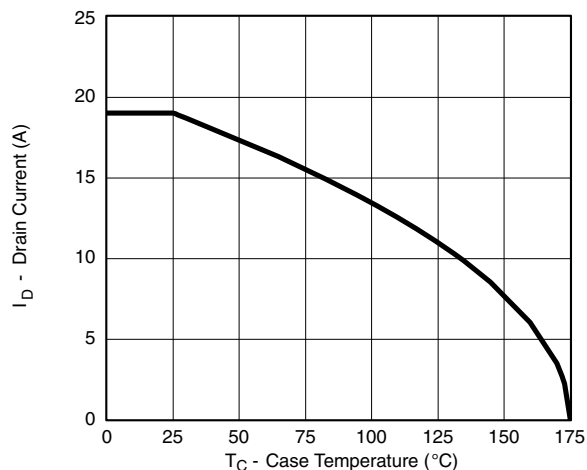


On-Resistance vs. Junction Temperature

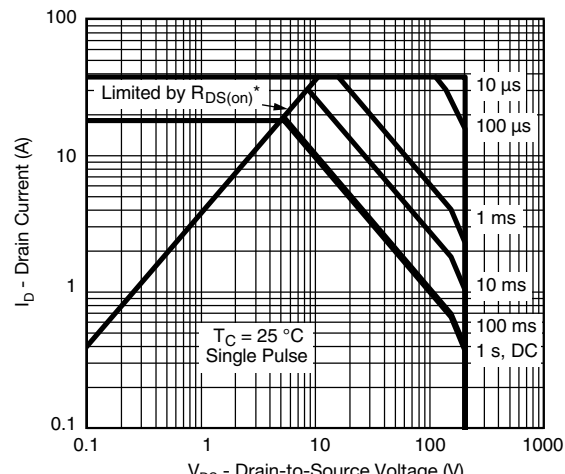


Source-Drain Diode Forward Voltage

## THERMAL RATINGS

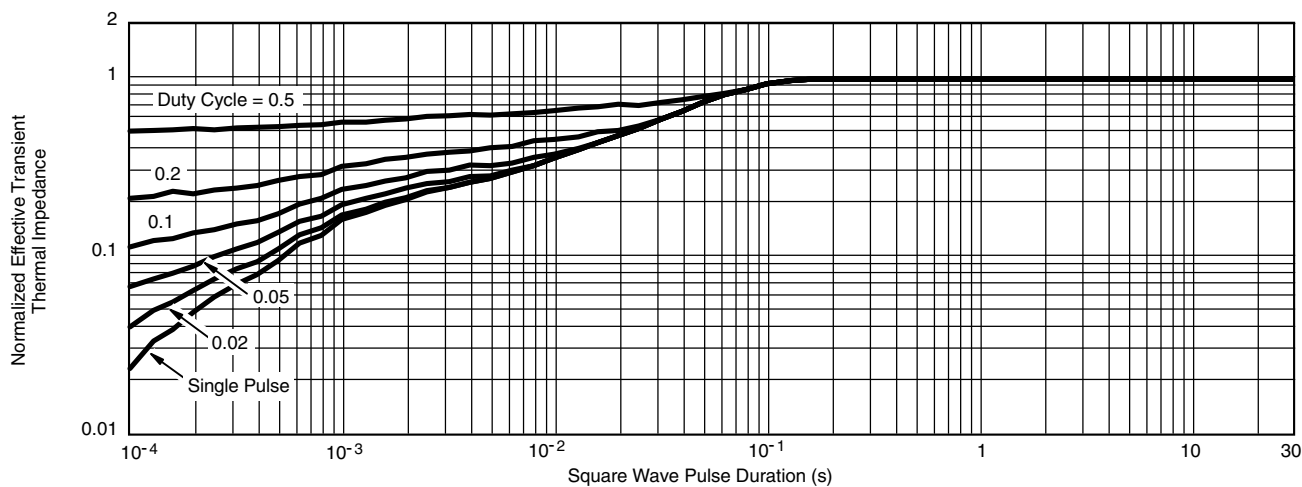


Maximum Avalanche Drain Current vs. Case Temperature



\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

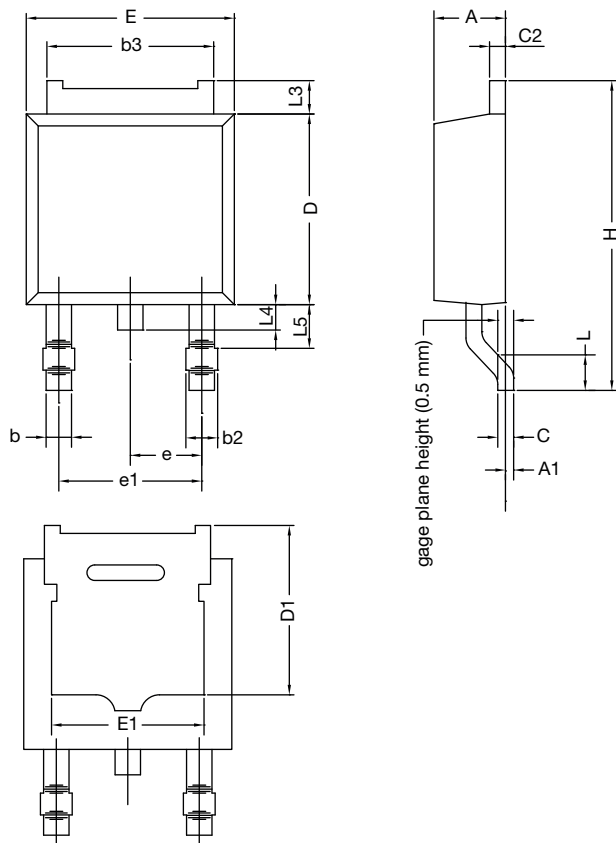
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?71767](http://www.vishay.com/ppg?71767).

## TO-252AA CASE OUTLINE

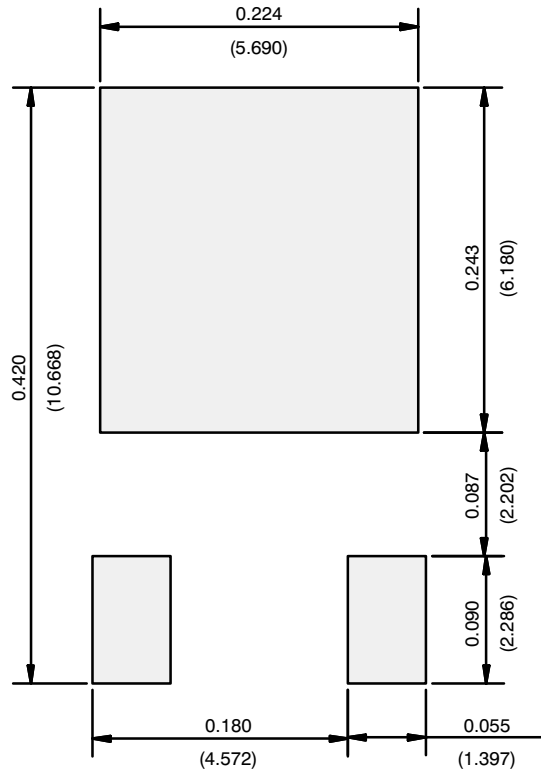


| DIM.                            | MILLIMETERS |       | INCHES    |       |
|---------------------------------|-------------|-------|-----------|-------|
|                                 | MIN.        | MAX.  | MIN.      | MAX.  |
| A                               | 2.18        | 2.38  | 0.086     | 0.094 |
| A1                              | -           | 0.127 | -         | 0.005 |
| b                               | 0.64        | 0.88  | 0.025     | 0.035 |
| b2                              | 0.76        | 1.14  | 0.030     | 0.045 |
| b3                              | 4.95        | 5.46  | 0.195     | 0.215 |
| C                               | 0.46        | 0.61  | 0.018     | 0.024 |
| C2                              | 0.46        | 0.89  | 0.018     | 0.035 |
| D                               | 5.97        | 6.22  | 0.235     | 0.245 |
| D1                              | 5.21        | -     | 0.205     | -     |
| E                               | 6.35        | 6.73  | 0.250     | 0.265 |
| E1                              | 4.32        | -     | 0.170     | -     |
| H                               | 9.40        | 10.41 | 0.370     | 0.410 |
| e                               | 2.28 BSC    |       | 0.090 BSC |       |
| e1                              | 4.56 BSC    |       | 0.180 BSC |       |
| L                               | 1.40        | 1.78  | 0.055     | 0.070 |
| L3                              | 0.89        | 1.27  | 0.035     | 0.050 |
| L4                              | -           | 1.02  | -         | 0.040 |
| L5                              | 1.14        | 1.52  | 0.045     | 0.060 |
| ECN: X12-0247-Rev. M, 24-Dec-12 |             |       |           |       |
| DWG: 5347                       |             |       |           |       |

### Note

- Dimension L3 is for reference only.

## RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads  
Dimensions in Inches/(mm)

[Return to Index](#)



## Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

## Material Category Policy

**Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.**

**Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.**

**Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.**

## Данный компонент на территории Российской Федерации

**Вы можете приобрести в компании MosChip.**

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

### Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: [info@moschip.ru](mailto:info@moschip.ru)

Skype отдела продаж:

moschip.ru

moschip.ru\_4

moschip.ru\_6

moschip.ru\_9